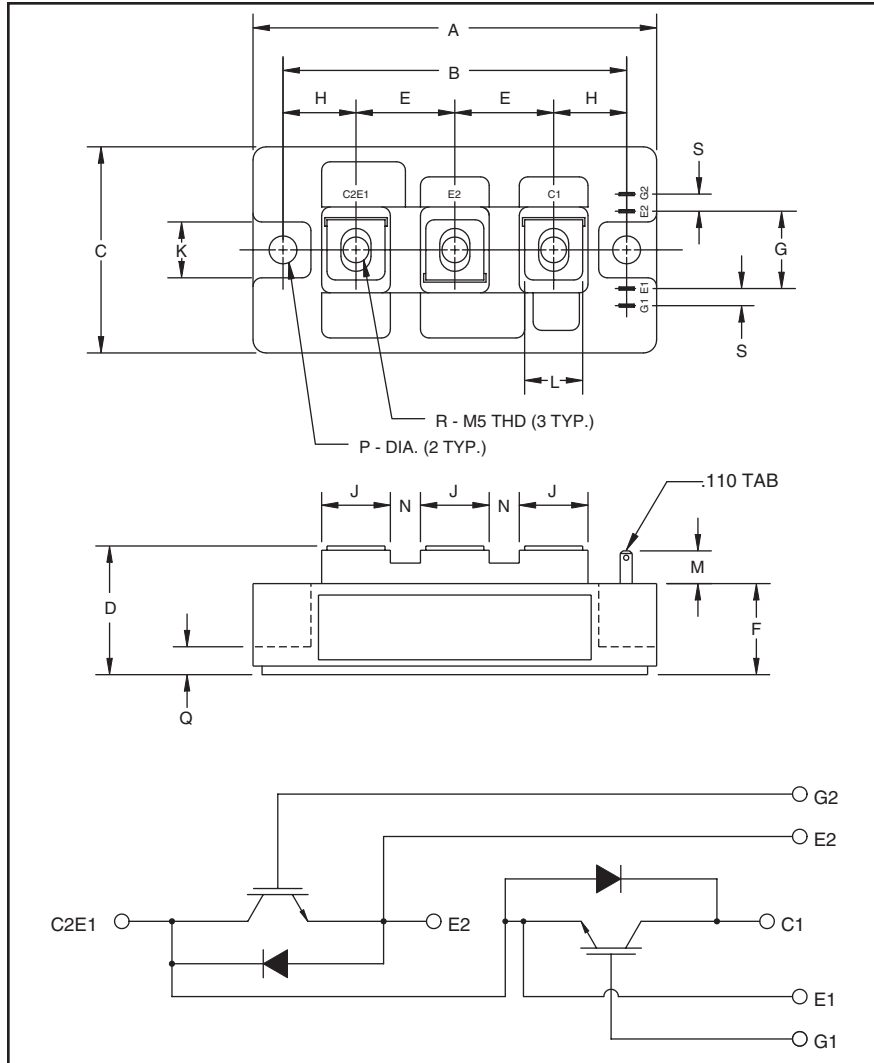


Dual IGBTMOD™ H-Series Module 200 Amperes/600 Volts



Dimensions	Inches	Millimeters
A	3.70	94.0
B	3.150±0.01	80.0±0.25
C	1.89	48.0
D	1.18 Max.	30.0 Max.
E	0.90	23.0
F	0.83	21.2
G	0.71	18.0
H	0.67	17.0
J	0.63	16.0

Dimensions	Inches	Millimeters
K	0.51	13.0
L	0.47	12.0
M	0.30	7.5
N	0.28	7.0
P	0.256 Dia.	Dia. 6.5
Q	0.31	8.0
R	M5 Metric	M5
S	0.16	4.0



Description:

Powerex IGBTMOD™ Modules are designed for use in switching applications. Each module consists of two IGBT Transistors in a half-bridge configuration with each transistor having a reverse-connected super-fast recovery free-wheel diode. All components and interconnects are isolated from the heat sinking baseplate, offering simplified system assembly and thermal management.

Features:

- ☐ Low Drive Power
- ☐ Low $V_{CE(sat)}$
- ☐ Discrete Super-Fast Recovery (70ns) Free-Wheel Diode
- ☐ High Frequency Operation (20-25kHz)
- ☐ Isolated Baseplate for Easy Heat Sinking

Applications:

- ☐ AC Motor Control
- ☐ Motion/Servo Control
- ☐ UPS
- ☐ Welding Power Supplies
- ☐ Laser Power Supplies

Ordering Information:

Example: Select the complete part module number you desire from the table below -i.e. CM200DY-12H is a 600V (V_{CES}), 200 Ampere Dual IGBTMOD™ Power Module.

Type	Current Rating Amperes	V_{CES} Volts (x 50)
CM	200	12

CM200DY-12H
Dual IGBTMOD™ H-Series Module
 200 Amperes/600 Volts

Absolute Maximum Ratings, $T_j = 25\text{ }^{\circ}\text{C}$ unless otherwise specified

Ratings	Symbol	CM200DY-12H	Units
Junction Temperature	T_j	-40 to 150	$^{\circ}\text{C}$
Storage Temperature	T_{stg}	-40 to 125	$^{\circ}\text{C}$
Collector-Emitter Voltage (G-E Short)	V_{CES}	600	Volts
Gate-Emitter Voltage	V_{GES}	± 20	Volts
Collector Current	I_C	200	Amperes
Peak Collector Current	I_{CM}	400*	Amperes
Diode Forward Current	I_F	200	Amperes
Diode Forward Surge Current	I_{FM}	400*	Amperes
Power Dissipation	P_d	780	Watts
Mounting Torque, M5 Terminal Screws	—	17	in-lb
Mounting Torque, M6 Mounting Screws	—	26	in-lb
Module Weight (Typical)	—	270	Grams
V Isolation	V_{RMS}	2500	Volts

* Pulse width and repetition rate should be such that device junction temperature does not exceed the device rating.

Static Electrical Characteristics, $T_j = 25\text{ }^{\circ}\text{C}$ unless otherwise specified

Characteristics	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Collector-Cutoff Current	I_{CES}	$V_{CE} = V_{CES}, V_{GE} = 0V$	—	—	1.0	mA
Gate Leakage Current	I_{GES}	$V_{GE} = V_{GES}, V_{CE} = 0V$	—	—	0.5	μA
Gate-Emitter Threshold Voltage	$V_{GE(th)}$	$I_C = 20mA, V_{CE} = 10V$	4.5	6.0	7.5	Volts
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = 200A, V_{GE} = 15V$	—	2.1	2.8**	Volts
		$I_C = 200A, V_{GE} = 15V, T_j = 150^{\circ}\text{C}$	—	2.15	—	Volts
Total Gate Charge	Q_G	$V_{CC} = 300V, I_C = 200A, V_{GE} = 15V$	—	600	—	nC
Diode Forward Voltage	V_{FM}	$I_E = 200A, V_{GE} = 0V$	—	—	2.8	Volts

** Pulse width and repetition rate should be such that device junction temperature rise is negligible.

Dynamic Electrical Characteristics, $T_j = 25\text{ }^{\circ}\text{C}$ unless otherwise specified

Characteristics	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Input Capacitance	C_{ies}	$V_{GE} = 0V, V_{CE} = 10V$	—	—	20	nF
Output Capacitance	C_{oes}		—	—	7	nF
Reverse Transfer Capacitance	C_{res}		—	—	4	nF
Inductive	Turn-on Delay Time	$V_{CC} = 300V, I_C = 200A, V_{GE1} = V_{GE2} = 15V, R_G = 3.1\Omega$	—	—	200	ns
Load	Rise Time		—	—	550	ns
Switch	Turn-off Delay Time		—	—	300	ns
Time	Fall Time		—	—	300	ns
Diode Reverse Recovery Time	t_{rr}	$I_E = 200A, di_E/dt = -400\mu s$	—	—	110	ns
Diode Reverse Recovery Charge	Q_{rr}	$I_E = 200A, di_E/dt = -400\mu s$	—	0.54	—	μC

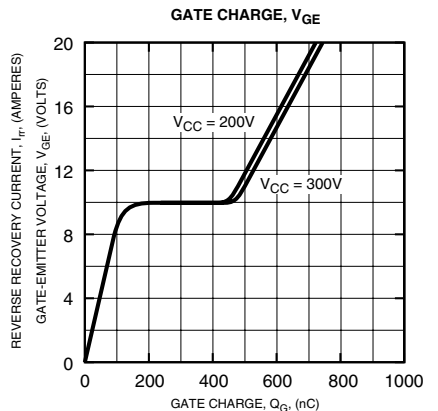
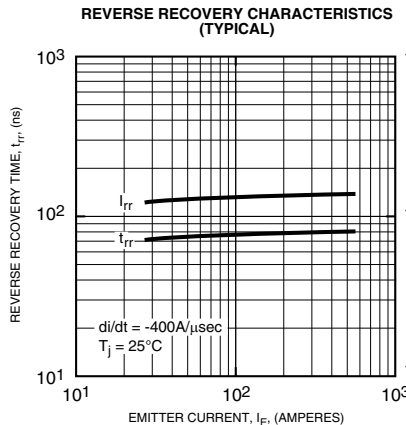
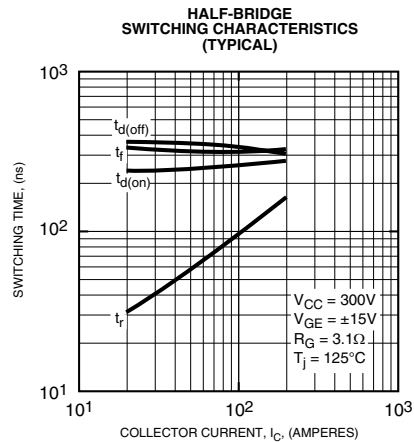
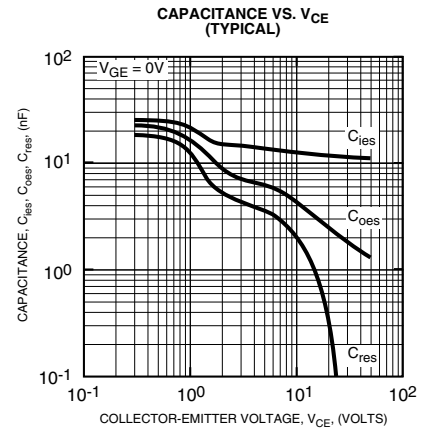
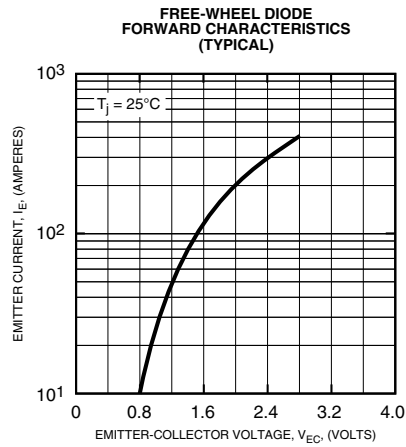
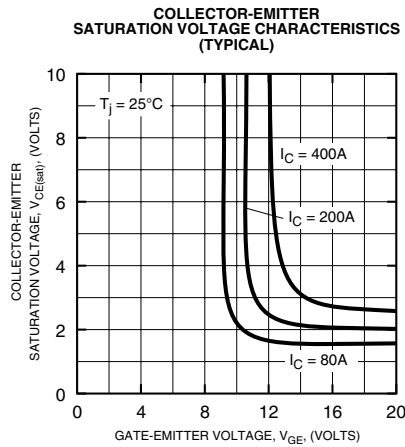
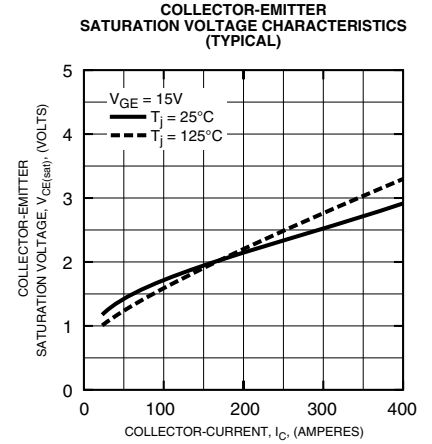
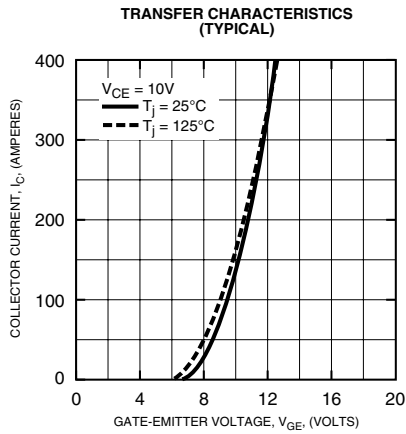
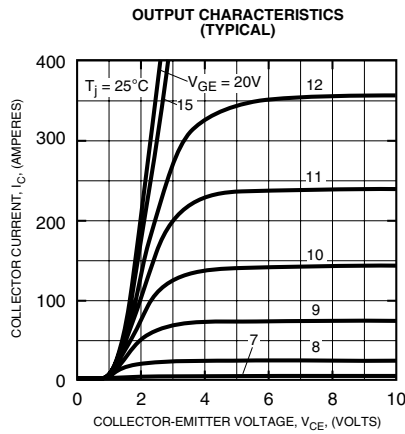
Thermal and Mechanical Characteristics, $T_j = 25\text{ }^{\circ}\text{C}$ unless otherwise specified

Characteristics	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Thermal Resistance, Junction to Case	$R_{th(j-c)}$	Per IGBT	—	—	0.16	$^{\circ}\text{C/W}$
Thermal Resistance, Junction to Case	$R_{th(j-c)}$	Per FWDi	—	—	0.35	$^{\circ}\text{C/W}$
Contact Thermal Resistance	$R_{th(c-f)}$	Per Module, Thermal Grease Applied	—	—	0.065	$^{\circ}\text{C/W}$

CM200DY-12H

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